

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	47.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	395.00 +/- 7.00 μ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00 μ m	Guaranteed by Process
	7.0	Flatness (SBIR)	<1.00 μ m	20mm x 20mm, no partials, b/side ref, 100% UA
	8.0	Bow	<60.00 μ m	ADE to ASTM F534
	9.0	Warp	<60.00 μ m	ADE to ASTM F657
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	3mm	
HandleSilicon	12.0	Handle Growth Method	FZ	Wafer Vendor
	13.0	Handle Carbon Concentration	< 2e16 atcm-3 new ASTM	Wafer Vendor
	14.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	15.0	Handle Thickness	380.00 +/- 5.00 μ m	ADE, 100%
	16.0	Handle Doping Type	N	Wafer Vendor
	17.0	Handle Dopant	Phosphorous	Wafer Vendor
	18.0	Handle Resistivity	2 - 10 Ohmcm	Wafer Vendor
	19.0	Backside Finish	Lapped and Etched with oxide and lasermark (see lasermark spec below)	Wafer Vendor
BuriedOxide	20.0	Oxide Type	Thermal	
	21.0	Oxide Thickness	6,000.00 +/- 300.00 A	Nanospec centre point, 4%
	22.0	Oxide formed on	Handle Wafer	
DeviceSilicon	23.0	Device Growth Method	CZ	Wafer Vendor
	24.0	Oxygen Concentration	< 8 e17 at/cm3 new ASTM	Wafer Vendor
	25.0	Carbon Concentration	< 2e16 atcm-3 new ASTM	Wafer Vendor
	26.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	27.0	Nominal Thickness	15.00 +/- 1.00 μ m	Filmetrics, 100% 9-Pt (note3)
	28.0	Distance to device silicon edge from wafer edge	<= 1.5mm	Typical by Process
	29.0	Device Doping Type	P	Wafer Vendor
	30.0	Device Dopant	Boron	Wafer Vendor
	31.0	Device Resistivity	0.05 - 0.1Ohm-cm	Wafer Vendor
	32.0	Voids	0	Bright Light, 100% (note 2)
	33.0	Scratches	none	Bright Light, 100% (note 2)
	34.0	Haze	none	Bright Light, 100% (note 2)

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Category**Parameter****Specification****Measurement Method**

DeviceSilicon

35.0

LPD Count

<30 @ 0.3um

Tencor Particle Counter

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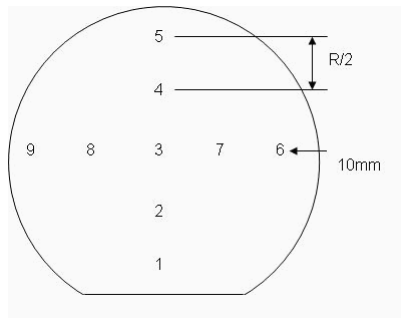
Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information